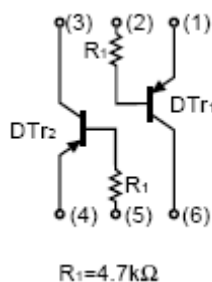
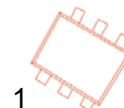


## DIGITAL TRANSISTOR (PNP+PNP)

### FEATURES

- Two DTA143T chips in a package
- Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.

### External circuit


**SOT-563**


### MARKING: B3

### Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{(BR)CBO}$	-50	V
Collector-emitter voltage	$V_{(BR)CEO}$	-50	V
Emitter-base voltage	$V_{(BR)EBO}$	-5	V
Collector current	$I_C$	-100	mA
Collector Power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

### Electrical characteristics ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-50			V	$I_C=-50\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-50			V	$I_C=-1\text{mA}$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5			V	$I_E=-50\mu\text{A}$
Collector cut-off current	$I_{CBO}$			-0.5	$\mu\text{A}$	$V_{CB}=-50\text{V}$
Emitter cut-off current	$I_{EBO}$			-0.5	$\mu\text{A}$	$V_{EB}=-4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$			-0.3	V	$I_C=-5\text{mA}, I_B=-2.5\text{mA}$
DC current transfer ratio	$h_{FE}$	100		600		$V_{CE}=-5\text{V}, I_C=-1\text{mA}$
Input resistance	$R_1$	3.29	4.7	6.11	K $\Omega$	
Transition frequency	$f_T$		250		MHz	$V_{CE}=10\text{V}, I_E=-5\text{mA}, f=100\text{MHz}$